

Description

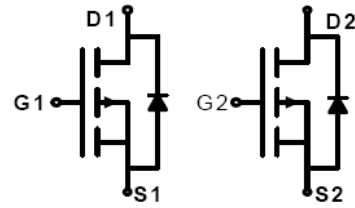
The G2003 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

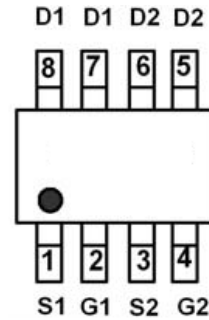
- $V_{DS} = 200V, I_D = 2.5A$
 $R_{DS(ON)} < 580m\Omega @ V_{GS}=10V$ (Typ:520m Ω)
- High density cell design for ultra low $R_{ds(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

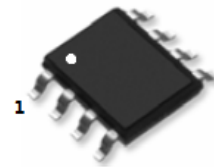
- Power switching application
- Hard switched and high frequency circuits
- LED



Schematic diagram



Marking and pin assignment



SOP-8 view

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	2.5 A	
Drain Current-Pulsed ^(Note 1)	I_{DM}	8	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=200V, V_{GS}=0V$	-	-	1	μA

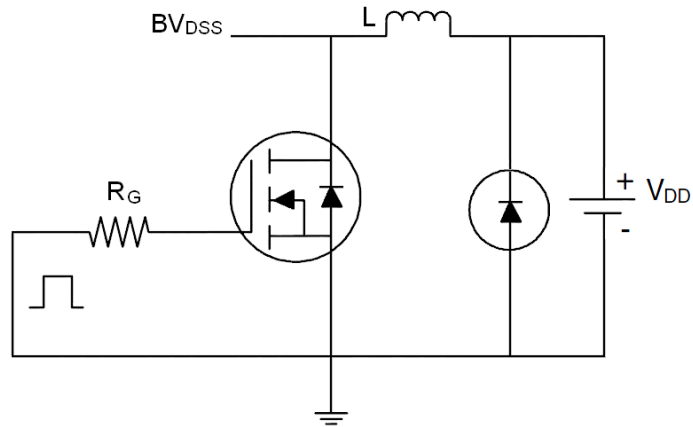
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	2.2	3.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2A$	-	520	580	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=15V, I_D=2A$	-	8	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	580	-	PF
Output Capacitance	C_{OSS}		-	90	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	3	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=100V, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	12	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t_f		-	15	-	nS
Total Gate Charge	Q_g	$V_{DS}=100V, I_D=2A,$ $V_{GS}=10V$	-	12	-	nC
Gate-Source Charge	Q_{gs}		-	2.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=2A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	2.5	A

Notes:

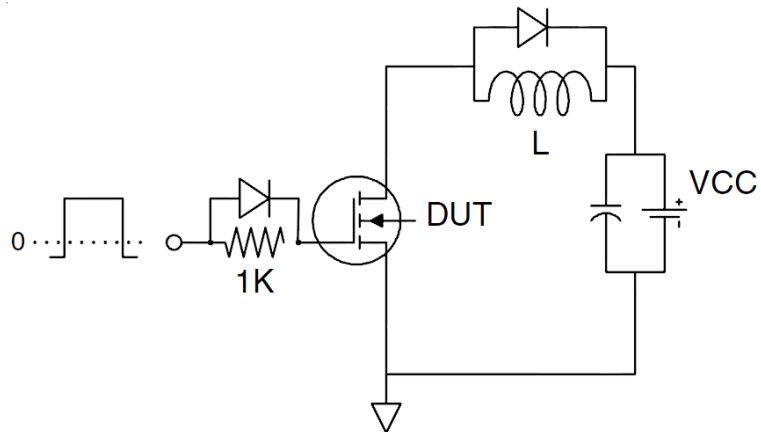
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

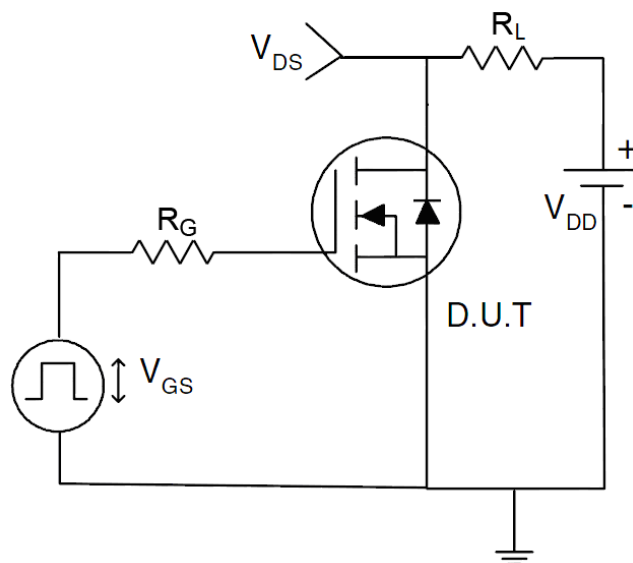
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

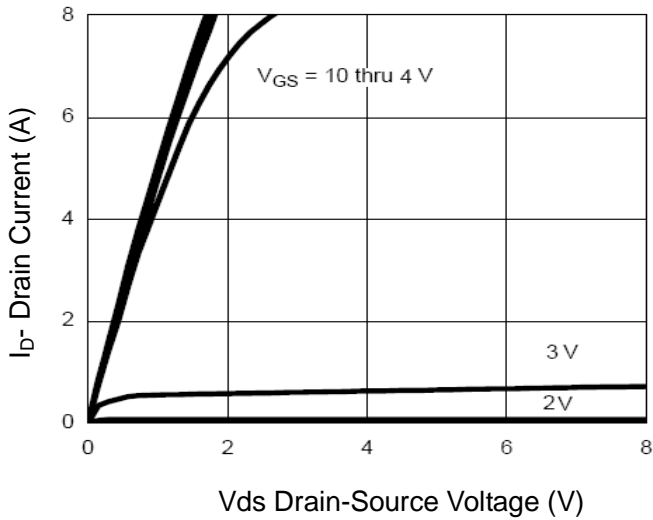


Figure 1 Output Characteristics

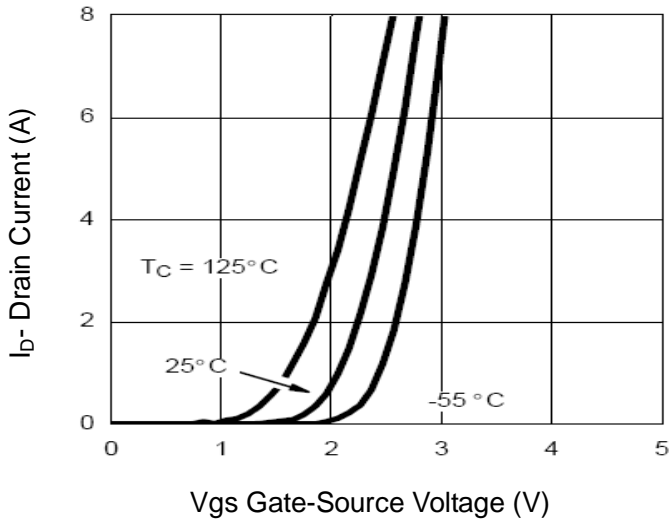


Figure 2 Transfer Characteristics

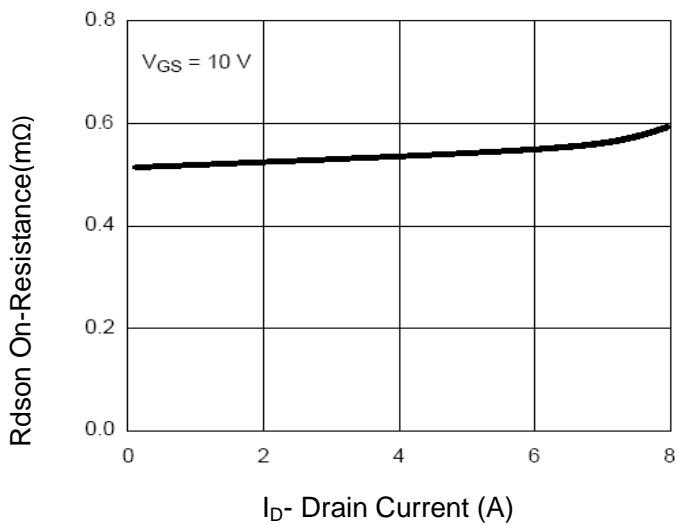


Figure 3 Rdson- Drain Current

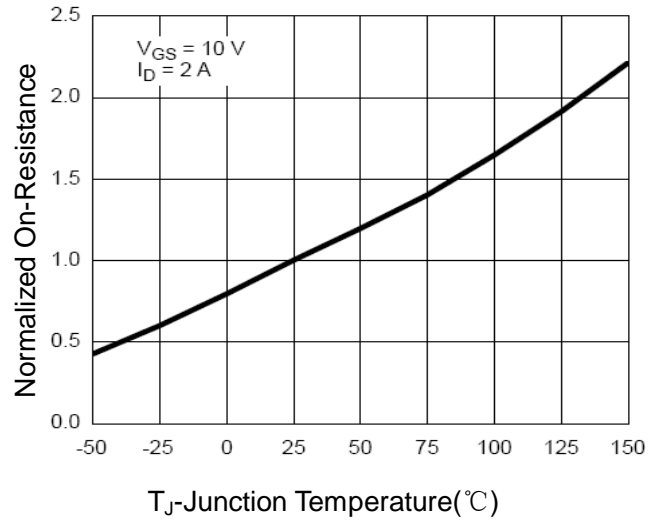


Figure 4 Rdson-Junction Temperature

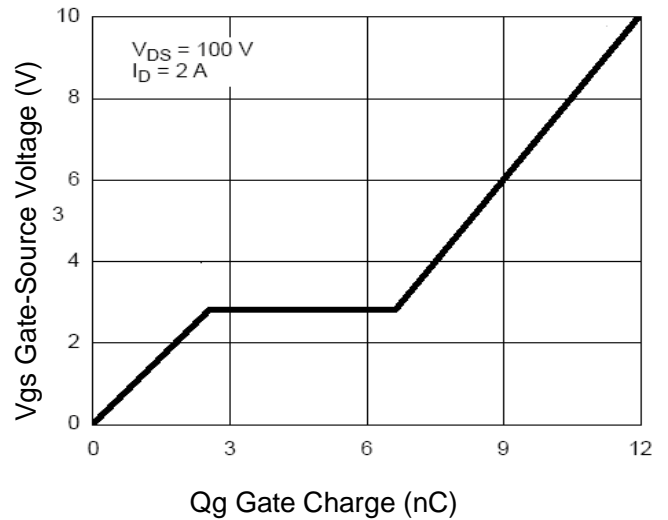


Figure 5 Gate Charge

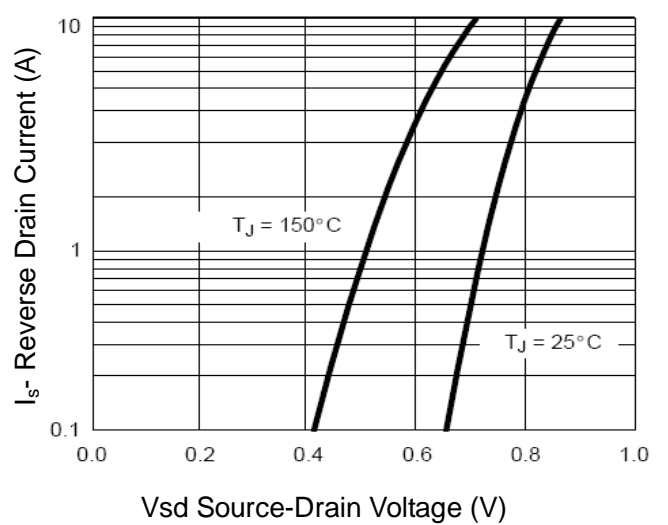


Figure 6 Source- Drain Diode Forward

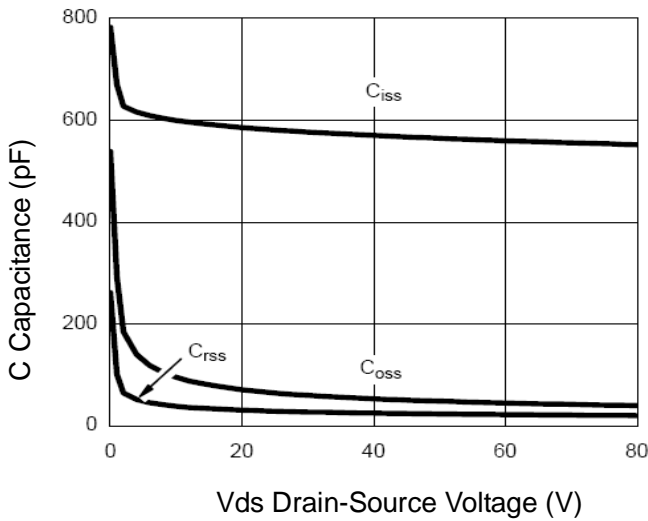


Figure 7 Capacitance vs Vds

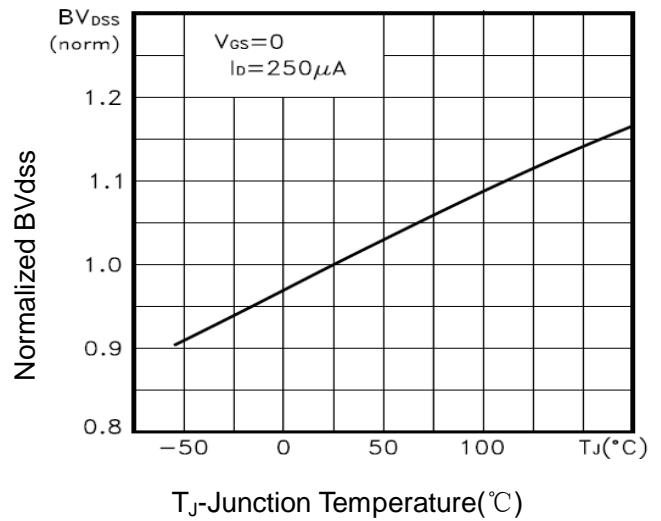


Figure 9 BV_{DSS} vs Junction Temperature

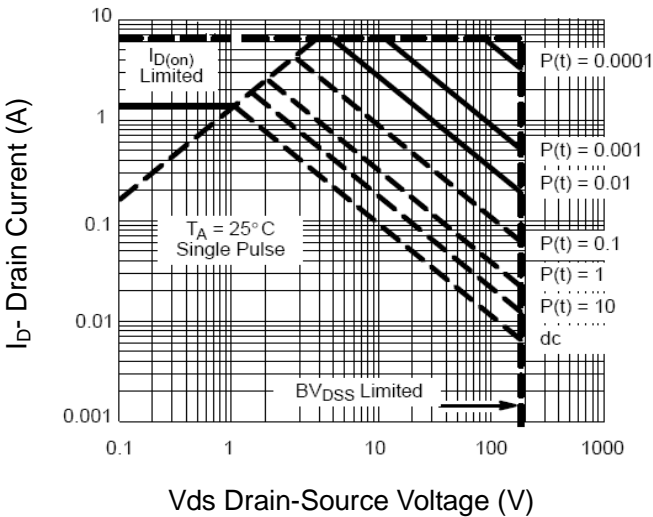


Figure 8 Safe Operation Area

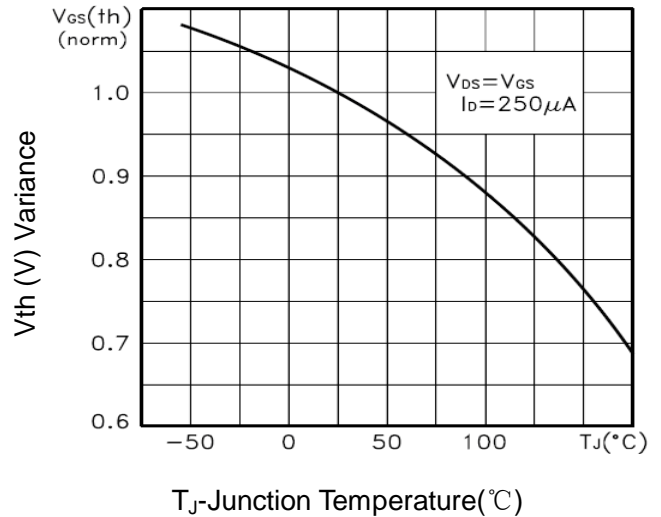


Figure 10 $V_{GS(th)}$ vs Junction Temperature

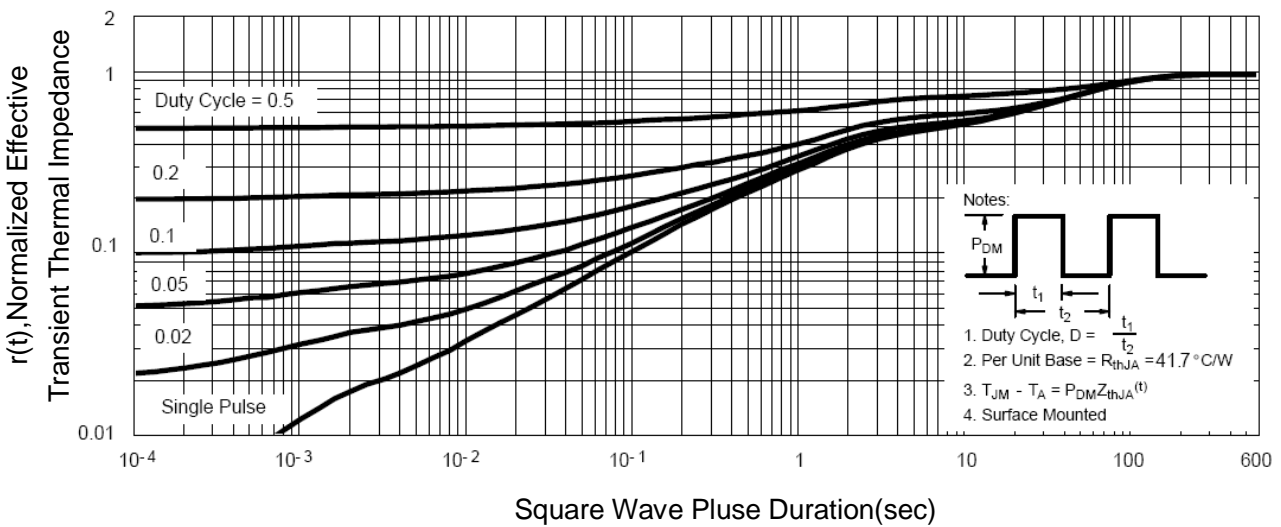


Figure 11 Normalized Maximum Transient Thermal Impedance